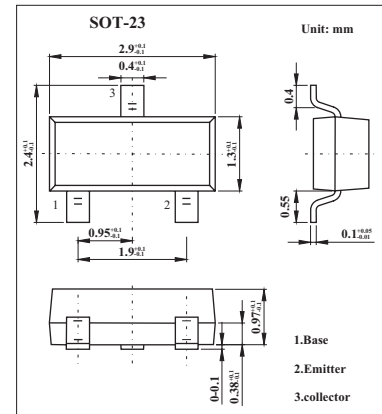


Silicon NPN Epitaxial

2SC2462

■ Features

- Low frequency amplifier.



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector-base voltage	V _{CB0}	50	V
Collector-emitter voltage	V _{CEO}	40	V
Emitter-base voltage	V _{EBO}	5	V
Collector current	I _C	100	mA
Collector dissipation	P _C	150	mW
Junction temperature	T _j	150	°C
Storage temperature	T _{stg}	-55 to +150	°C

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V _{CB0}	I _C = 10μA, I _E = 0	50			V
Collector-emitter breakdown voltage	V _{CEO}	I _C = 1mA, R _{BE} = ∞	40			V
Emitter-base breakdown voltage	V _{EBO}	I _E = 10μA, I _C = 0	5			V
Base-emitter voltage	V _{BE}	V _{CE} = 12V, I _C = 2mA			0.75	V
Collector cutoff current	I _{CBO}	V _{CB} = 30V, I _E = 0			0.5	μA
Emitter cutoff current	I _{EBO}	V _{EB} = 2V, I _C = 0			0.5	μA
DC current gain	h _{FE}	V _{CE} = 12V, I _C = 2mA	100		500	
Collector-emitter saturation voltage	V _{CE(sat)}	I _C = 10mA, I _B = 1mA			0.2	V

■ hFE Classification

Marking	LB	LC	LD
Rank	B	C	D
hFE	100~200	160~320	250~500

2SC2462

■ Typical Characteristics

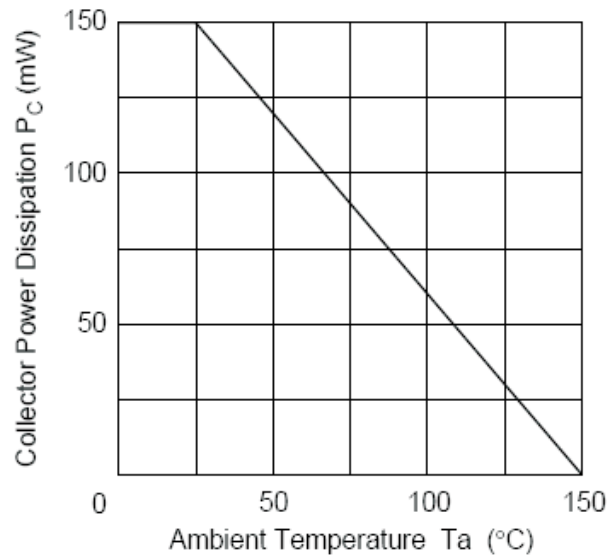


Fig.1 Maximum Collector Dissipation Curve